

## Plastic-Encapsulate Transistors

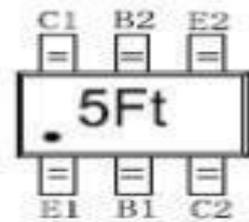
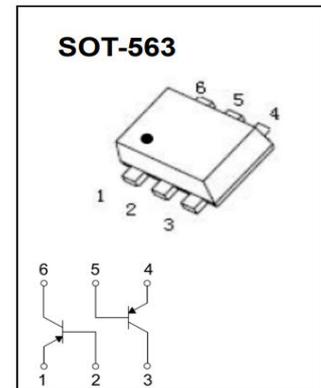
DUAL TRANSISTOR (PNP+PNP)

### FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

**MAXIMUM RATINGS**( $T_a=25^{\circ}\text{C}$  unless otherwise noted)

symbol	Parameter	Value
$V_{CB0}$	Collector- Base Voltage	-80
$V_{CE0}$	Collector-Emitter Voltage	-65
$V_{EB0}$	Emitter-Base Voltage	-5
$I_c$	Collector Current -Continuous	-0.1
$P_c$	Collector Power Dissipation	0.2
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625
$T_J, T_{STG}$	Operation Junction and Storage Temperature Range	-55~+150



**ELECTRICAL CHARACTERISTICS**( $T_a= 25^{\circ}\text{C}$  unless otherwise specified)

Parameter	symbol	Test conditions	Min	Typ	Max	Unit
Collector.base breakdown voltage	$V_{(BR)CBO}$	$I_c=-10\mu\text{A}, I_E=0$	-80			V
Collector.emitter breakdown voltage	$V_{(BR)CEO}$	$I_c=-10\text{mA}, I_B=0$	-65			V
Emitter.base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_c=0$	-5			V
Collector cut.off current	$I_{CBO}$	$V_{CB}=-30\text{V}, I_E=0$			-15	nA
Emitter cut.off current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_c=0$			-100	nA
DC current gain	$h_{FE}$	$V_{CE}=-5\text{V}, I_c=-2\text{mA}$	200		450	
Collector.emitter saturation voltage	$V_{CE(sat)}$	$I_c=-10\text{mA}, I_B=-0.5\text{mA}$			-0.1	V
		$I_c=-100\text{mA}, I_B=-5\text{mA}^*$			-0.3	V
Base.emitter saturation voltage	$V_{BE(sat)}$	$I_c=-10\text{mA}, I_B=-0.5\text{mA}$		0.7		V
output Capacitance	$C_{obo}$	$V_{CB}=-10\text{V}, f=1\text{MHz}, I_E=0$			2.5	pF
Current Gain.Bandwidth Product	$f_T$	$V_{CE}=-5\text{V}, I_c=-10\text{mA}, f=100\text{MHz}$	100			MHz

## Typical Characteristics

